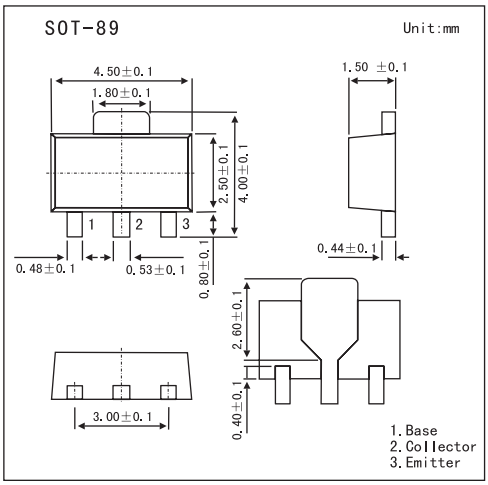
Silicon PNP Epitaxial

2SB1000



■ Features

● Low frequency amplifier.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	-25	V
Collector to emitter voltage	V_{CEO}	-20	V
Emitter to base voltage	V_{EBO}	-5	V
Collector current	I_C	-1	A
peak collector current	I_{CP} *	-1.5	A
Collector power dissipation	P_C	1	W
Junction temperature	Tj	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

* PW ⩽ 10 ms; d ⩽ 0.02.

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector to base breakdown voltage	$V_{(BR)CBO}$	I_C = -10 μA, I_E = 0	-25			V
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	I_C = -1 mA, R_{BE} = ∞	-20			V
Emitter to base breakdown voltage	$V_{(BR)EBO}$	I_E = -10 μA, I_C = 0	-5			V
Collector cutoff current	I_{CBO}	V_{CB} = -20 V, I_E = 0			-0.1	μA
Emitter cutoff current	I_{EBO}	V_{EB} = -4 V, I_C = 0			-0.1	μA
DC current transfer ratio *	h_{FE}	V_{CE} = -2 V, I_C = -0.5 A	85		240	
Collector to emitter saturation voltage *	$V_{CE(sat)}$	I_C = -0.8 A, I_B = -0.08 A		-0.2	-0.3	V
Base to emitter saturation voltage *	$V_{BE(sat)}$	I_C = -0.8 A, I_B = -0.08 A		-0.94	-1.1	V
Gain bandwidth product	f_T	V_{CE} = -2 V, I_C = -0.15 A		200		MHz
Collector output capacitance	C_{ob}	V_{CB} = -10 V, I_E = 0 f=1MHz		38		pF

■ h_{FE} Classification

Marking	AH	AJ
hFE	85～170	120～240